

IFW



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Nick Lindert Et Al.

Serial No.: 10/692,696

Filed: October 24, 2003

For: Epitaxially Deposited  
Source/Drain

§ Group Art Unit: 2811

§

§

§

§

§

§

§

§

Examiner: Cuong Quang Nguyen

Atty. Dkt. No.: ITL.1063US  
(P18030)

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

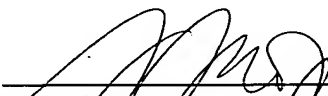
INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicant submits the references listed on the attached form PTO 1449, copies of which are enclosed. A copy of a communication dated April 6, 2005 from a foreign patent office in a counterpart application is also enclosed. I, the undersigned, hereby certify that each item of information contained in the Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement. Please apply any charges or credits to Deposit Account No. 20-1504 (ITL.1063US).

Respectfully submitted,

April 14, 2005  
Date

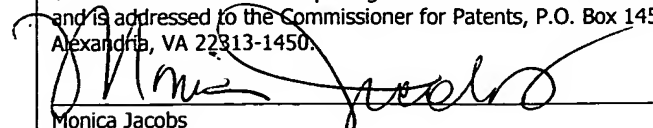
  
Timothy N. Trop, Reg. No. 28,994  
Trop, Pruner & Hu, P.C.  
8554 Katy Freeway, Ste. 100  
Houston, TX 77024  
713/468-8880  
713/468-8883 [fax]


Customer No.

**21906**

Date of Deposit: April 14, 2005

I hereby certify under 37 CFR 1.8(a) that this correspondence is being deposited with the United States Postal Service as **first class mail** with sufficient postage on the date indicated above and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

  
Monica Jacobs

 <p><b>INFORMATION DISCLOSURE CITATION</b> (Use several sheets if necessary)</p>	ATTY DOCKET NO. ITL.1063US (P18030)	SERIAL NO. 10/692,696
	APPLICANT(S): Nick Lindert et al.	
	FILING DATE: October 24, 2003	GROUP ART UNIT: 2811

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.	6,214,679	04/10/2001	Murthy et al.			
B.	6,342,421	01/29/2002	Mitani et al.			
C.	6,605,498	08/12/2003	Murthy et al.			
D.						
E.						

**U.S. PATENT APPLICATION PUBLICATIONS**

F.						
G.						
H.						
I.						
J.						

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
K.	JP 63 013379	06/21/1988	Japan			Abstract Only	
L.	WO 00/30169	05/25/2000	PCT				
M.							
N.							
O.							

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

P.	S. Gannavaram et al., <i>Low Temperature (<math>\leq 800^{\circ}\text{C}</math>) Recessed Junction Selective Silicon-Germanium Source/Drain Technology for sub-70 nm CMOS</i> ; International Electron Devices Meeting 2000, IEDM, Technical Digest, San Francisco, CA, Dec. 10-13, 2000, IEEE, US, Dec. 10, 2000, pgs. 437-440.
Q.	
R.	
S.	
T.	
U.	

EXAMINER	DATE CONSIDERED
----------	-----------------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.